

Silicon NPN Power Transistors

BU2515DF

DESCRIPTION

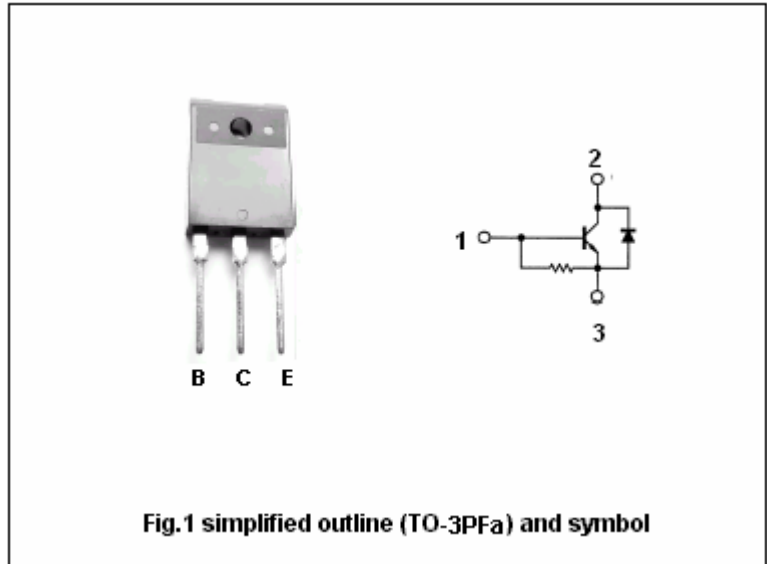
- With TO-3PFa package
- High voltage;high speed
- Built-in damper diode

APPLICATIONS

- For use in horizontal deflection circuits of PC monitors.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	V
I_C	Collector current (DC)		9	A
I_{CM}	Collector current (Pulse)		20	A
I_B	Base Collector current (DC)		5	A
I_{BM}	Base current (Pulse)		7.5	A
P_{tot}	Total power dissipation	$T_C=25^\circ\text{C}$	45	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _B =600mA ; I _C =0	7.5	13.5		V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =0.9A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =0.9A			1.0	V
I _{CES}	Collector cut-off current	V _{CE} =BV _{CES} ; V _{BE} =0 T _j =125°C			1.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0		130		mA
h _{FE-1}	DC current gain	I _C =1.0A ; V _{CE} =5V		13		
h _{FE-2}	DC current gain	I _C =4.5A ; V _{CE} =5V	5	8	10.2	
V _F	Diode forward voltage	I _F =4.5A			2.2	V

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PACKAGE OUTLINE

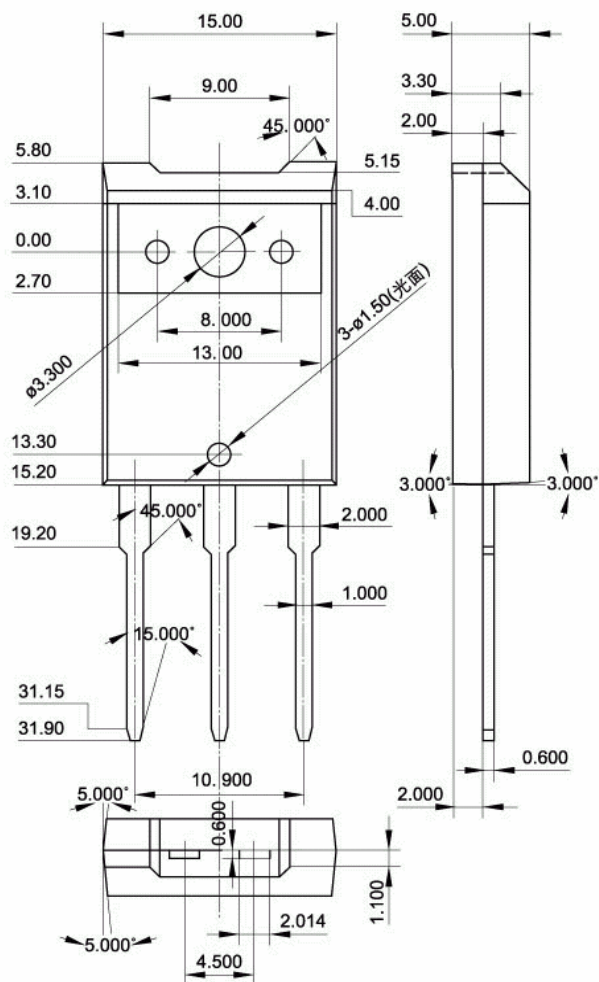


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)